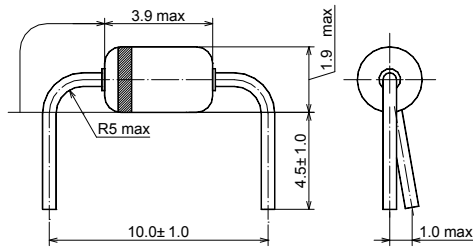


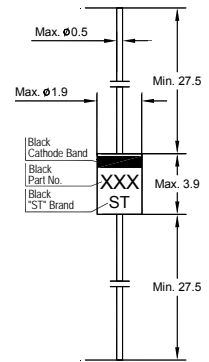
ST60P, ST60S

Silicon Schottky Barrier Diode

Characteristics equivalent to
1N60P and 1N60S



Glass case DO-35-1
Dimensions in mm



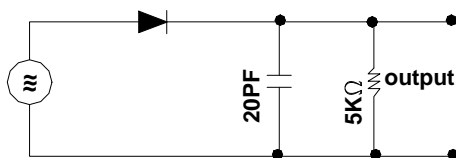
Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	I_O	50	mA
Peak Forward Current	I_{FM}	150	mA
Surge Forward Current	I_{surge}	500	mA
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	I_F	4	-	mA
Reverse Current at $V_R = 10\text{ V}$	ST60P	-	50	μA
	ST60S	-	100	μA
Rectification efficiency at $V_i = 2\text{ V}_{rms}$, $R = 5\text{ K}\Omega$, $C = 20\text{ pF}$, $f = 40\text{ MHz}$	η	55	-	%



Input 2Vrms

Rectification Efficiency Measurement Circuit

